

15V NPN MEDIUM POWER TRANSISTOR IN SOT23

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 2086 @3
- Weight: 0.008 grams (Approximate)

Features

- BV_{CEO} > 15V
- Maximum Continuous Collector Current I_C = 6A
- V_{CE(SAT)} < 30mV @ 1A
- R_{CE(SAT)} = 19mΩ Typical
- High Power Dissipation SOT23 Package
- High Peak Current
- Low Saturation Voltage
- 60V Forward Blocking Voltage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The ZTN23015CFHQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

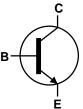
Applications

- DC DC Converters
- MOSFET and IGBT Gate Driving
- Motor Drive
- · Relay, Lamp and Solenoid Drive

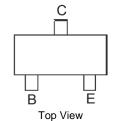
SOT23 (Type DN)



Top View



Device Symbol



Pin-Out

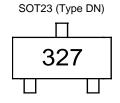
Ordering Information (Note 4)

-						
	Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
	ZTN23015CFHQTA	Automotive	327	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
 1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



327 = Product Type Marking Code



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEV}	60	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	6	Α
Base Current	I _B	1.2	Α
Peak Pulse Current	I _{CM}	12	Α

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 6)		0.73 5.84		
Power Dissipation	(Note 7)		1.05 8.4	W mW/°C	
Linear Derating Factor	(Note 8)	P _D	1.25 9.6		
	(Note 9)		1.81 14.5		
	(Note 6)		171		
The second Description of the Architect	(Note 7)	R ₀ JA	119	°C/W	
Thermal Resistance, Junction to Ambient	(Note 8)		100		
	(Note 9)		69		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Notes:

^{6.} For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operation in steady-state

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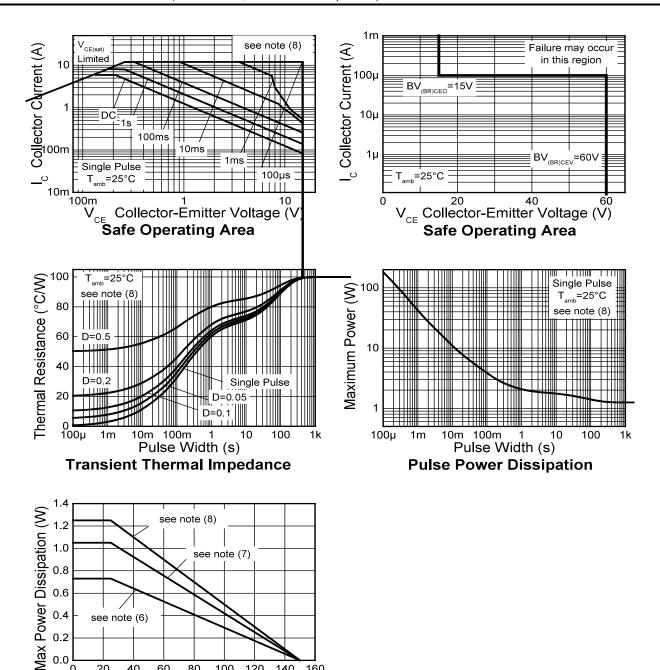
7. Mounted on 25mm × 25mm 1.6mm FR-4 PCB with a high coverage of single sided 2oz copper in still air conditions.

^{8.} Mounted on 50mm × 50mm 1.6mm FR-4 PCB with a high coverage of single sided 2oz copper in still air conditions.

^{9.} Same as note (8), except measured at t < 5 seconds.



Thermal Characteristics (@ TA = +25°C, unless otherwise specified.)



0.0

40 60 80 100 Temperature (°C)

Derating Curve

120

140



Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

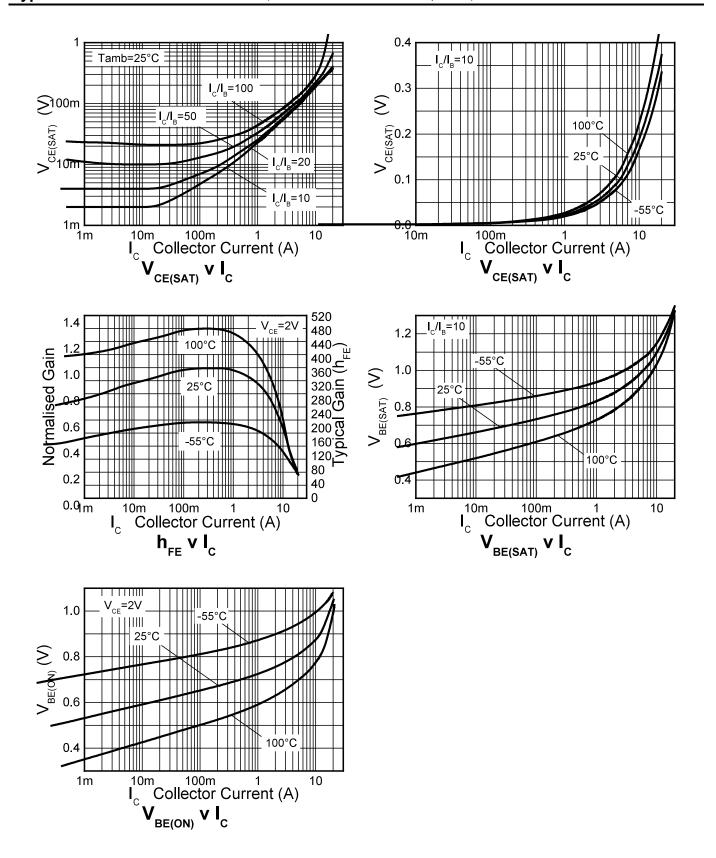
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	60	85	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV_CEV	60	85	_	V	I_C = 100μA, $R_{BE} \le 1$ k Ω or -1V < V_{BE} < 0.25V
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	15	23	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	_	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	_	< 1	20	nA	V _{CB} = 48V
Collector-Emitter Cutoff Current	I _{CEV}	_	_	100	nA	V_{CE} = 48V, $R_{BE} \le 1$ kΩ or -1V < V_{BE} < 0.25V
Emitter-Base Cutoff Current	I _{EBO}	_	< 1	10	nA	V _{EB} = 6V
		160	300	_		$I_C = 10$ mA, $V_{CE} = 2$ V
Static Forward Current Transfer Ratio (Note 10)	L	200	350	560		$I_C = 500 \text{mA}, V_{CE} = 2V$
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	190	330	_	_	$I_C = 3A$, $V_{CE} = 2V$
		150	280	_		$I_C = 6A$, $V_{CE} = 2V$
		_	7	15		$I_C = 0.1A, I_B = 5mA$
Collector-Emitter Saturation Voltage (Note 10)	V	_	22	30	mV	$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation voltage (Note 10)	$V_{CE(sat)}$	_	70	90	IIIV	$I_C = 3A$, $I_B = 60mA$
			130	180		$I_C = 6A$, $I_B = 120mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}		0.83	0.93	V	$I_C = 3A$, $I_B = 60mA$
base-Emilier Saturation voltage (Note 10)			0.89	0.98	V	$I_C = 6A$, $I_B = 120mA$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(on)}$	_	0.81	0.91	V	$I_C = 6A$, $V_{CE} = 2V$
Output Capacitance	Сово	_	56		pF	$V_{CB} = 10V, f = 1MHz$
Transition Frequency	f⊤	_	235	_	MHz	$V_{CE} = 2V$, $I_C = 500$ mA, f = 50MHz
Delay Time	t _d	_	15	_		
Rise Time	t _r	_	38.5	_	ns	$V_{CC} = 5V, I_{C} = 3A,$
Storage Time	t _{stg}		213	_		$I_{B1} = -I_{B2} = 150 \text{mA}$
Fall Time	t _f	_	19.7	_		

Note:

10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



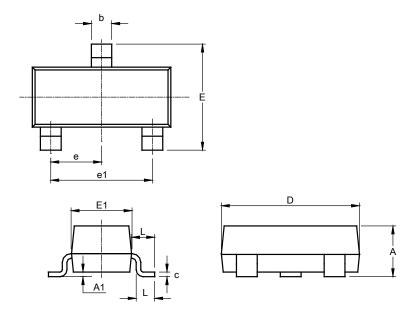
Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

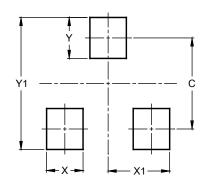
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23 (Type DN)						
Dim	Min	Max	Тур			
Α	0.89	1.12	1.00			
A1	0.01	0.10	0.05			
b	0.30 0.51 0.4					
С	0.08 0.20 0.10					
D	2.80	3.04	3.00			
Е	2.10	2.64	2.42			
E1	1.20 1.40 1.37					
е	0.95 REF					
e1	1.90 REF					
L	0.25	0.60	0.30			
L1	0.45	0.62	0.54			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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